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APPLICATION NO.	FILING DAT	TE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
09/754,323	01/05/2001		Masatoshi Akagawa	1081.1102	3680
21171	7590 01/	/09/2004		EXAMINER	
	IALSEY LLP			NGUYEN,	KHIEM D
SUITE 700 1201 NEW Y	ORK AVENUE,	. N.W.		ART UNIT	PAPER NUMBER
WASHINGTON, DC 20005				2823	

DATE MAILED: 01/09/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

			AL					
	Application No.	Applicant(s)						
	09/754,323	AKAGAWA, MASA	AKAGAWA, MASATOSHI					
Office Action Summary	Examiner	Art Unit						
	Khiem D Nguyen	2823						
The MAILING DATE of this communication apperiod for Reply	pears on the cover she	et with the correspondence add	dress					
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a replet if NO period for reply is specified above, the maximum statutory period Failure to reply within the set or extended period for reply will, by statute. Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).  Status	136(a). In no event, however, m ly within the statutory minimum will apply and will expire SIX (6) e, cause the application to become	nay a reply be timely filed  of thirty (30) days will be considered timely ) MONTHS from the mailing date of this come ABANDONED (35 U.S.C. § 133).						
1) Responsive to communication(s) filed on 05	November 2003 .							
2a)☐ This action is <b>FINAL</b> . 2b)⊠ Th	nis action is non-final.							
3) Since this application is in condition for allow closed in accordance with the practice under <b>Disposition of Claims</b>			e merits is					
4)⊠ Claim(s) <u>4-6,14 and 16-21</u> is/are pending in t	ne application.							
4a) Of the above claim(s) is/are withdra	4a) Of the above claim(s) is/are withdrawn from consideration.							
5) Claim(s) is/are allowed.								
6)⊠ Claim(s) <u>4-6,14 and 16-21</u> is/are rejected.								
7) Claim(s) is/are objected to.	Claim(s) is/are objected to.							
8) Claim(s) are subject to restriction and/o	or election requirement	t.						
Application Papers								
9)☐ The specification is objected to by the Examine	er.							
10)⊠ The drawing(s) filed on <u>05 January 2001</u> is/are	: a)⊠ accepted or b)□	objected to by the Examiner.						
Applicant may not request that any objection to the								
11) The proposed drawing correction filed on		disapproved by the Examine	er.					
If approved, corrected drawings are required in re	•							
12) The oath or declaration is objected to by the Ex	caminer.							
Priority under 35 U.S.C. §§ 119 and 120								
13) Acknowledgment is made of a claim for foreig	n priority under 35 U.S	S.C. § 119(a)-(d) or (f).						
a)⊠ All b)□ Some * c)□ None of:								
<ol> <li>Certified copies of the priority document</li> </ol>	ts have been received	•						
2. Certified copies of the priority document	ts have been received	in Application No						
<ul> <li>3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> </ul>								
14) Acknowledgment is made of a claim for domest	ic priority under 35 U.S	S.C. § 119(e) (to a provisional	application).					
a) The translation of the foreign language pro	• •							
Attachment(s)								
<ol> <li>Notice of References Cited (PTO-892)</li> <li>Notice of Draftsperson's Patent Drawing Review (PTO-948)</li> <li>Information Disclosure Statement(s) (PTO-1449) Paper No(s)</li> </ol>	5) 🔲 Notic	rview Summary (PTO-413) Paper No( ce of Informal Patent Application (PTO er:						

### **DETAILED ACTION**

### Continued Examination Under 37 CFR 1.114

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on November 05, 2003 has been entered. A new rejection is made as set forth in this Office Action. Claims (4-6, 14, 16, 17, and 18-21) are pending in the application.

## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in-
- (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effect under this subsection of a national application published under section 122(b) only if the international application designating the United States was published under Article 21(2)(a) of such treaty in the English language; or
- (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that a patent shall not be deemed filed in the United States for the purposes of this subsection based on the filing of an international application filed under the treaty defined in section 351(a).
- 1. Claims 14 and 16 are rejected under 35 U.S.C. 102(e) as being anticipated by Akram et al. (U.S. Patent No. 6,235,554).

In re claim 14, <u>Akram</u> discloses a semiconductor device comprising (col. 3, line 64 to col. 5, line 34 and **FIGS. 1-4**):

a first insulating layer (42, 44, 46) having vias (16, 40) extending therethrough (FIG. 1) (col. 4, lines 16-50);

a first conductive layer 26 comprising a first wiring patterns embedded within the first insulating layer (42, 46) (lowermost package 10C in FIGS. 1-4);

a second conductive layer (middle package 10B) comprising a second wiring patterns on the first insulating layer, the wiring patterns of the second conductive layer being electrically connected to the wiring patterns of the first conductive layer through the vias (16, 40) of the first insulating layer (col. 4, line 60 to col. 5, line 34 and FIGS. 1-4);

a semiconductor element 14 embedded in the first insulating layer and electrically connected to the wiring patterns of the first conductive layer (col. 5, lines 9-17 and FIG. 4); and

a second insulating layer having a semiconductor element 14, electrically connected to the wiring pattern of the second conductive layer, embedded therein and embedding further therein the second conductive layer (col. 4, line 60 to col. 5, line 34 and FIGS. 1-4).

In re claim 16, <u>Akram</u> discloses wherein one or more of the wiring patterns of the first conductive layer 26 is/are electrically connected to one or more of the wiring patterns of the second conductive layer through corresponding vias (16, 40) (col. 4, lines 16-50).

2. Claim 17 is rejected under 35 U.S.C. 102(e) as being anticipated by Akram et al. (U.S. Patent No. 6,235,554).

In re claim 17, **Akram** discloses a semiconductor device comprising (col. 3, line 64 to col. 5, line 34 and **FIGS. 1-4**):

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a substrate 50;

a first set of conductors 26 comprising a first conductive layer formed on the substrate (lowermost package 10C in FIGS. 1-4);

a first insulating layer (42, 44, 46) formed on the first set of conductors and having vias (16, 40) extending therethrough (FIG. 1) (col. 4, lines 16-50), the first insulating layer having at least one semiconductor element and the first set of conductors embedded therein;

a second set of conductors (middle package 10B) comprising a second conductive layer formed on the first insulating layer and extending through the vias therein; and

a second insulating layer formed on the second set of conductors and having vias extending therethrough, the second insulating layer having at least one semiconductor element 14, and portions of the second set of conductors embedded therein (col. 4, line 60 to col. 5, line 34 and FIGS. 1-4);

wherein one or more of the first set of conductors 26 is/are electrically connected to the at least one semiconductor element 14 embedded in the first insulating layer (42, 44, 46) and through corresponding said vias (16, 40) to one or more of the second set of conductors and one or more of the second set of conductors is/are electrically connected to the at least one semiconductor element embedded in the second insulating layer and through corresponding vias to one or more of the first set of conductors (col. 3, line 64 to col. 5, line 34 and FIGS. 1-4).

3. Claims 18-21 are rejected under 35 U.S.C. 102(e) as being anticipated by Akram et al. (U.S. Patent No. 6,235,554).

In re claim 18, <u>Akram</u> discloses a semiconductor device comprising (col. 3, line 64 to col. 5, line 34 and FIGS. 1-4):

a substrate 50 having a main surface;

plural device layers stacked, in succession, on the main surface of the substrate, each device layer comprising:

a conductive layer 26 comprising a wiring pattern, (lowermost package 10C in FIGS. 1-4);

a semiconductor element 14 electrically connected to the wiring patterns (col. 5, lines 9-17 and FIG. 4); and

a single insulating layer 44 respectively associated with and embedding threin the semiconductor element and the respective conductor layer having conductive vias (16, 40) extending therethrough (FIG. 1) (col. 4, lines 16-50), and

the wiring pattern of the conductive layer of each successive, stacked device layer being formed on an upper main surface of the single insulating layer of the respective, underlying device and respective wiring patterns of the conductive layers of the plural stacked device layers being selectively electrically interconnected through the corresponding vias of the respective, single insulating layers of the stacked, plural device layers (col. 3, line 64 to col. 5, line 34 and **FIGS. 1-4**).

In re claim 19, <u>Akram</u> discloses wherein: the semiconductor elements 14 are commonly disposed within the respective insulating layers (42, 44, 46) and aligned in the plural, stacked device layers (FIGS. 1 and 4).

In re claim 20, <u>Akram</u> discloses wherein the semiconductor device according to claim 18, further comprising: plural semiconductor elements 14 in each of the plural device layers and commonly disposed therein so as to be in aligned relationship in the stacked layers (FIGS. 1 and 4).

In re claim 21, <u>Akram</u> discloses wherein the semiconductor device according to claim 18, wherein each insulating layer (44, 42) surrounds and covers substantially all of each outer surface of the semiconductor element 14 embedded therein (FIGS. 1 and 4).

## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 4-6 are rejected under 35 U.S.C. 103(a) as being unpatentable over Akram et al. (U.S. Patent No. 6,235,554) as applied to claims 18-21 above, and further in view of Itabashi et al. (U.S. Patent No. 6,300,244).

In re claim 4, it is held that the selection of the semiconductor element thickness is obvious because it is a matter of determining optimum process conditions by routine experimentation with a limited number of species. In re Jones, 162USPQ 224 (CCPA 1955)(the selection of optimum ranges within prior art general conditions is obvious) and In re Boesch, 205 USPQ 215 (CCPA1980)(discovery of optimum value of result effective variable in a known process is obvious). Note that the specification contains no disclosure of either the critical nature of the claimed dimensions of any unexpected

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results arising there from. Where patentability is aid to be based upon particular chosen dimensions or upon another variable recited in a claim, the Applicant must show that the chosen dimensions are critical. <u>In re Woodruff</u>, 919 F.2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990).

In re claims 5-6, <u>Akram</u> does not explicitly disclose wherein each semiconductor element is electrically connected by flip chip mounting to respective wiring pattern and wherein each semiconductor element is electrically connected via an anisotropically conductive film to respective wiring pattern.

<u>Itabashi</u> discloses in figures 1-11 and related text wherein each semiconductor element 1 is electrically connected by flip chip mounting to respective wiring pattern, and inherently, by an anisotropically conductive film (figure 10 and col. 17, lines 10-30). It would have been obvious to one of ordinary skill in the art at the time of the invention to combine the teaching of Itabashi with the method of Akram in order to provide excellent anti-shock resistance and connection reliability (col. 3, lines 35-45).

#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Khiem D Nguyen whose telephone number is (703) 306-0210. The examiner can normally be reached on Monday-Friday (8:00 AM - 5:00 PM).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on (703) 306-2794. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 305-3432 for regular communications and (703) 305-3432 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

K.N. January 6, 2004

> W. David Coleman-Primary Examiner